Hex Schmitt-Trigger Inverter with LSTTL Compatible Inputs

High-Performance Silicon-Gate CMOS

The 74HCT14 may be used as a level converter for interfacing TTL or NMOS outputs to high-speed CMOS inputs.

The HCT14 is useful to "square up" slow input rise and fall times. Due to the hysteresis voltage of the Schmitt trigger, the HCT14 finds applications in noisy environments.

Features

- Output Drive Capability: 10 LSTTL Loads
- TTL/NMOS-Compatible Input Levels
- Outputs Directly Interface to CMOS, NMOS, and TTL
- Operating Voltage Range: 4.5 to 5.5 V
- Low Input Current: 1.0 μA
- In Compliance With the JEDEC Standard No. 7A Requirements
- ESD Performance: HBM > 2000 V; Machine Model > 200 V
- Chip Complexity: 72 FETs or 18 Equivalent Gates
- These are Pb-Free Devices



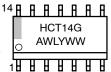
ON Semiconductor®

http://onsemi.com

MARKING DIAGRAMS



SOIC-14 D SUFFIX CASE 751A





1

TSSOP-14 DT SUFFIX CASE 948G



HCT14 = Device Code

A = Assembly Location

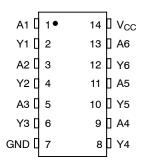
L, WL = Wafer Lot Y = Year W, WW = Work Week G or ■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

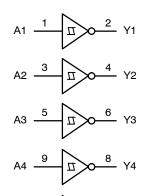
PIN ASSIGNMENT



FUNCTION TABLE

Input	Output
A	Y
L H	ГΗ

LOGIC DIAGRAM



A6
$$\frac{13}{\square}$$
 $\frac{12}{\square}$ Y6 $Y = \overline{A}$ PIN 14 = V_{CC} PIN 7 = GND

ORDERING INFORMATION

Device	Package	Shipping [†]
74HCT14DR2G	SOIC-14 (Pb-Free)	2500 / Tape & Reel
74HCT14DTR2G	TSSOP-14*	

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. *This package is inherently Pb-Free.

MAXIMUM RATINGS

Symbol	P	arameter	Value	Unit
V _{CC}	DC Supply Voltage	(Referenced to GND)	-0.5 to +7.0	V
VI	DC Input Voltage	(Referenced to GND)	-0.5 to V_{CC} $+0.5$	V
Vo	DC Output Voltage	(Referenced to GND)	-0.5 to V_{CC} $+0.5$	V
I _{IK}	DC Input Diode Current		±20	mA
I _{OK}	DC Output Diode Current		±25	mA
ΙO	DC Output Sink Current		±25	mA
I _{CC}	DC Supply Current per Supply Pin		±50	mA
I _{GND}	DC Ground Current per Ground Pin		±50	mA
T _{STG}	Storage Temperature Range		-65 to +150	°C
TL	Lead Temperature, 1 mm from Case for	or 10 Seconds	260	°C
TJ	Junction Temperature under Bias		+ 150	°C
$\theta_{\sf JA}$	Thermal Resistance	SOIC TSSOP	125 170	°C/W
P _D	Power Dissipation in Still Air at 85°C	SOIC TSSOP	500 450	mW
MSL	Moisture Sensitivity		Level 1	
F _R	Flammability Rating	Oxygen Index: 30% – 35%	UL 94 V-0 @ 0.125 in	
V _{ESD}	ESD Withstand Voltage	Human Body Model (Note 1) Machine Model (Note 2)	>2000 >200	V
I _{Latchup}	Latchup Performance	Above V _{CC} and Below GND at 85°C (Note 3)	±300	mA

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- 1. Tested to EIA/JESD22-A114-A.
- 2. Tested to EIA/JESD22-A115-A.
- Tested to EIA/JESD78.
- 4. For high frequency or heavy load considerations, see the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
V _{CC}	DC Supply Voltage (Referenced to GN	D) 4.5	5.5	V
V _I , V _O	DC Input Voltage, Output Voltage (Referenced to GN	D) 0	V _{CC}	V
T _A	Operating Temperature, All Package Types	- 55	+ 125	°C
t _r , t _f	Input Rise and Fall Time (Figure 1)	-	(Note 5)	ns

- 5. No Limit when V_I ≈ 50% V_{CC}, I_{CC} > 1 mA.
 6. Unused inputs may not be left open. All inputs must be tied to a high–logic voltage level or a low–logic input voltage level.

DC ELECTRICAL CHARACTERISTICS (Voltages Referenced to GND)

				Temperature Limit						
			v_{cc}	-55°C to 25°C ≤8		5°C	≤12	25°C	1	
Symbol	Parameter	Test Conditions	(V)	Min	Max	Min	Max	Min	Max	Unit
V_{T+} max	Maximum Positive-Going Input Threshold Voltage	V_O = 0.1 V or V_{CC} – 0.1 V $\left I_{out}\right $ \leq 20 μA	4.5 5.5		1.9 2.1		1.9 2.1		1.9 2.1	٧
V_{T+} min	Minimum Positive-Going Input Threshold Voltage	V_O = 0.1 V or V_{CC} – 0.1 V $\left I_{out}\right $ \leq 20 μA	4.5 5.5	1.2 1.4		1.2 1.4		1.2 1.4		٧
V_{T-} max	Maximum Negative-Going Input Threshold Voltage	V_O = 0.1 V or V_{CC} – 0.1 V $\left I_{out}\right $ \leq 20 μA	4.5 5.5		1.2 1.4		1.2 1.4		1.2 1.4	
V_{T-} min	Minimum Negative-Going Input Threshold Voltage	$V_O = 0.1 \text{ V or } V_{CC} - 0.1 \text{ V}$ $\left I_{out}\right \le 20 \mu\text{A}$	4.5 5.5	0.5 0.6		0.5 0.6		0.5 0.6		
V _H max	Maximum Hysteresis Voltage	V_O = 0.1 V or V_{CC} – 0.1 V $\left I_{out}\right $ \leq 20 μA	4.5 5.5		1.4 1.5		1.4 1.5		1.4 1.5	
V _H min	Minimum Hysteresis Voltage	V_O = 0.1 V or V_{CC} – 0.1 V $\left I_{out}\right $ \leq 20 μA	4.5 5.5	0.4 0.4		0.4 0.4		0.4 0 4		
V _{OH}	Minimum High-Level Output Voltage	$V_I < V_{T-}$ min $ I_{out} \le 20 \mu A$	4.5 5.5	4.4 5.4		4.4 5.4		4.4 5.4		٧
		$V_{I} < V_{T-}$ min $ I_{out} \le 4.0 \text{ mA}$	4.5	3.98		3.84		3.7		
V _{OL}	Maximum Low-Level Output Voltage	$V_1 \ge V_{T+} max$ $ I_{out} \le 20 \mu A$	4.5 5.5		0.1 0.1		0.1 0.1		0.1 0.1	V
		$V_l \ge V_{T+} max$ $ I_{out} \le 4.0 \text{ mA}$	4.5		0.26		0.33		0.4	
I _{IK}	Maximum Input Leakage Current	V _I = V _{CC} or GND	5.5		±0.1		±1.0		±1.0	μΑ
I _{CC}	Maximum Quiescent Supply Current (per package)	$V_I = V_{CC}$ or GND $I_{out} = 0 \mu A$	5.5		2.0		20		40	μΑ
				≥ -55°C 25°C to 12		5°C				
ΔI_{CC}	Additional Quiescent Supply Current	V_{I} = 2.4 V, Any One Input V_{I} = V_{CC} or GND, Other Inputs I_{out} = 0 μA	5.5	2.9 2.4		2.4		mA		

^{7.} Information on typical parametric values can be found in the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

AC CHARACTERISTICS ($C_L = 50 \text{ pF}$; Input $t_r = t_f = 6.0 \text{ ns}$)

				Guaranteed Limit						
				-55°C	to 25°C	≤8	5°C	≤12	5°C	
Symbol	Parameter	Test Conditions	Figures	Min	Max	Min	Max	Min	Max	Unit
t _{PLH} , t _{PHL}	Maximum Propagation Delay, Input A to Output Y (L to H)	$V_{CC} = 5.0 \text{ V} \pm 10\%$ $C_L = 50 \text{ pF}, \text{ Input } t_r = t_f = 6.0 \text{ ns}$	1 & 2		32		40		48	ns
t _{TLH} , t _{THL}	Maximum Output Transition Time, Any Output	$V_{CC} = 5.0 \text{ V} \pm 10\%$ $C_L = 50 \text{ pF, Input } t_r = t_f = 6.0 \text{ ns}$	1 & 2		15		19		22	ns

^{8.} For propagation delays with loads other than 50 pF, and information on typical parametric values, see the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

		Typical @ 25°C, V _{CC} = 5.0 V	
C_{PD}	Power Dissipation Capacitance, per Inverter (Note 9)	32	рF

^{9.} Used to determine the no-load dynamic power consumption: P_D = C_{PD} V_{CC}²f + I_{CC} V_{CC}. For load considerations, see the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

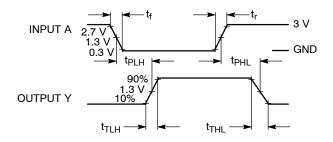
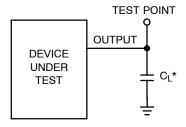


Figure 1. Switching Waveforms

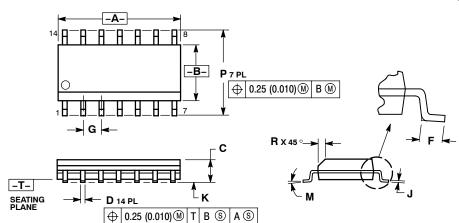


*Includes all probe and jig capacitance.

Figure 2. Test Circuit

PACKAGE DIMENSIONS

SOIC-14 CASE 751A-03 **ISSUE H**



- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

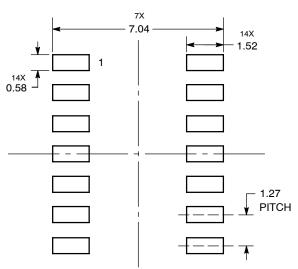
 3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.

 4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.

 5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	8.55	8.75	0.337	0.344
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27	BSC	0.050	BSC
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
М	0 °	7 °	0 °	7 °
Р	5.80	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

SOLDERING FOOTPRINT*

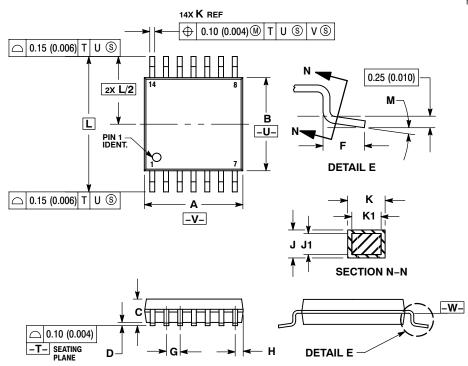


DIMENSIONS: MILLIMETERS

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

TSSOP-14 CASE 948G-01 **ISSUE B**



NOTES:

- OTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.

 2. CONTROLLING DIMENSION: MILLIMETER.

 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.

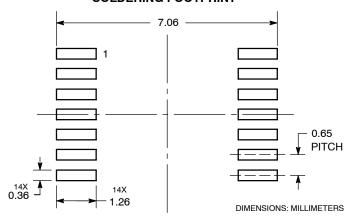
 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.

 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.

 6. TERMINAL NUMBERS ARE SHOWN FOR
- 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY. 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE –W–.

	MILLIN	IETERS	INC	HES
DIM	MIN	MAX	MIN	MAX
Α	4.90	5.10	0.193	0.200
В	4.30	4.50	0.169	0.177
С		1.20		0.047
D	0.05	0.15	0.002	0.006
F	0.50	0.75	0.020	0.030
G	0.65	BSC	0.026	BSC
Н	0.50	0.60	0.020	0.024
J	0.09	0.20	0.004	0.008
J1	0.09	0.16	0.004	0.006
K	0.19	0.30	0.007	0.012
K1	0.19	0.25	0.007	0.010
L	6.40	BSC	0.252 BSC	
М	0 °	8 °	0 °	8 °

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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